

N-channel 100 V, 22 mΩ logic level MOSFET in LFPAK56

7 November 2016

Product data sheet

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. **Features and benefits**

- Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating •
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

#### Applications 3.

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching •

#### Quick reference data 4.

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	49	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	147	W
Static charac	teristics		1				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	17.4	22	mΩ
Dynamic cha	racteristics						
Q <sub>GD</sub>	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$		-	13.3	-	nC

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UT 4
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package	ckage					
	Name	Description	Version				
BUK9Y22-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y22-100E	92210E

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	10	V
		Pulsed; T <sub>j</sub> ≤ 175 °C	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	147	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	49	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	35	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3		-	197	А

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode	·				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	49	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	197	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 49 \; {\sf A};  {\sf V}_{\sf sup} \le 100 \; {\sf V};  {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{\sf j(init)} = 25 \; {}^\circ{\sf C}; \; {\sf unclamped}; \\ & {\sf Fig. 4} \end{split}$	[3][4]	-	80.8	mJ

- [1]
- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering  $\rm T_{j}$  and or  $\rm V_{GS}$ [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]

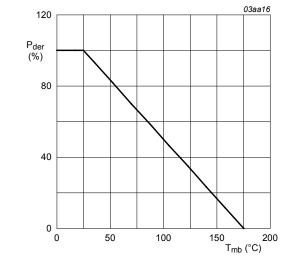


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

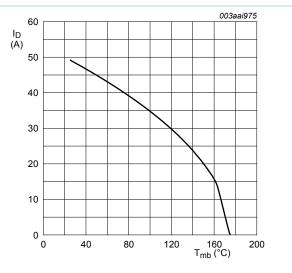


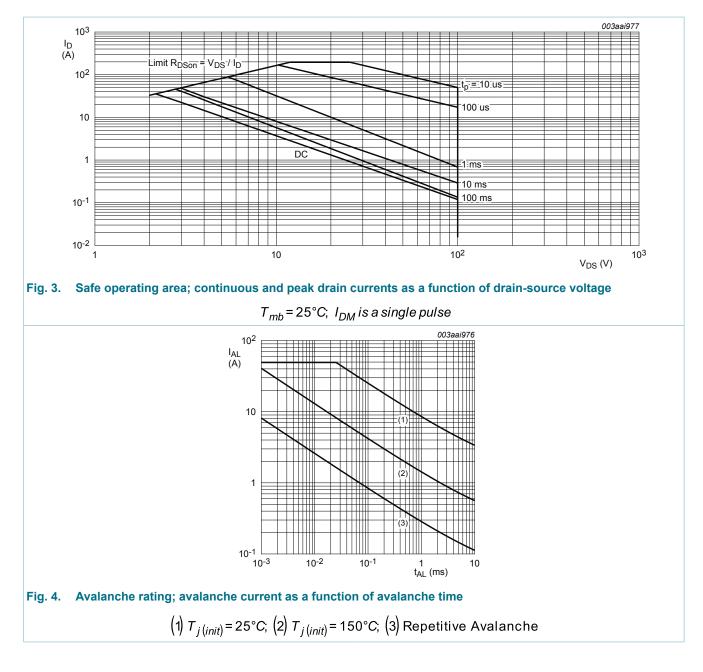
Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$ 

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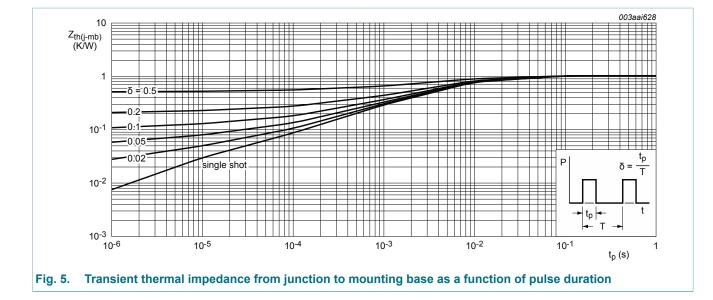


### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	1.02	K/W

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#### N-channel 100 V, 22 m $\Omega$ logic level MOSFET in LFPAK56



### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·	I			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9;</u> Fig. 10	1.4	1.7	2.1	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; Fig. 9$	0.5	-	-	V
I <sub>DSS</sub> drain leakage curren	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.04	10	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	17.4	22	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	16.8	21.5	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	60.7	mΩ
Dynamic cl	naracteristics		· · ·			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 5 V;	-	35.8	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	6.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	13.3	-	nC

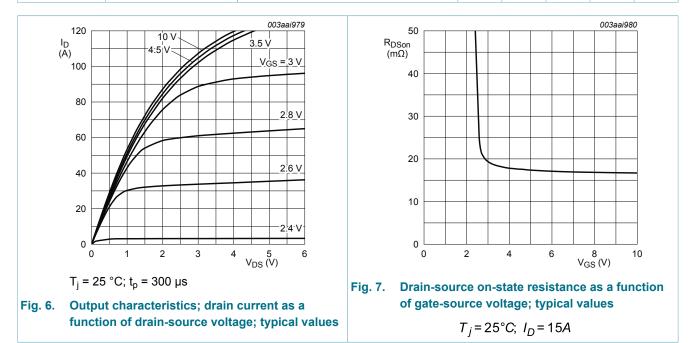
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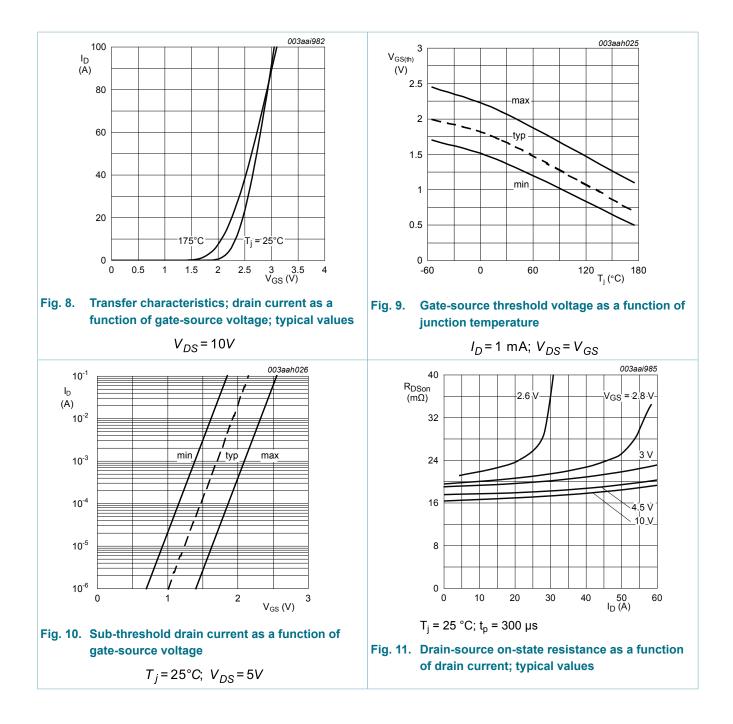
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;		-	3480	4640	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	212	254	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS} = 80 \text{ V}; \text{ R}_1 = 5 \Omega; \text{ V}_{GS} = 5 \text{ V};$		-	130	178	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 80 \text{ V}; \text{ R}_{L} = 5 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	15.8	-	ns
t <sub>r</sub>	rise time			-	32.3	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	53.4	-	ns
t <sub>f</sub>	fall time	-		-	31.1	-	ns
Source-dra	ain diode	1	1	1			
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 15 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	37	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C		-	52	-	nC



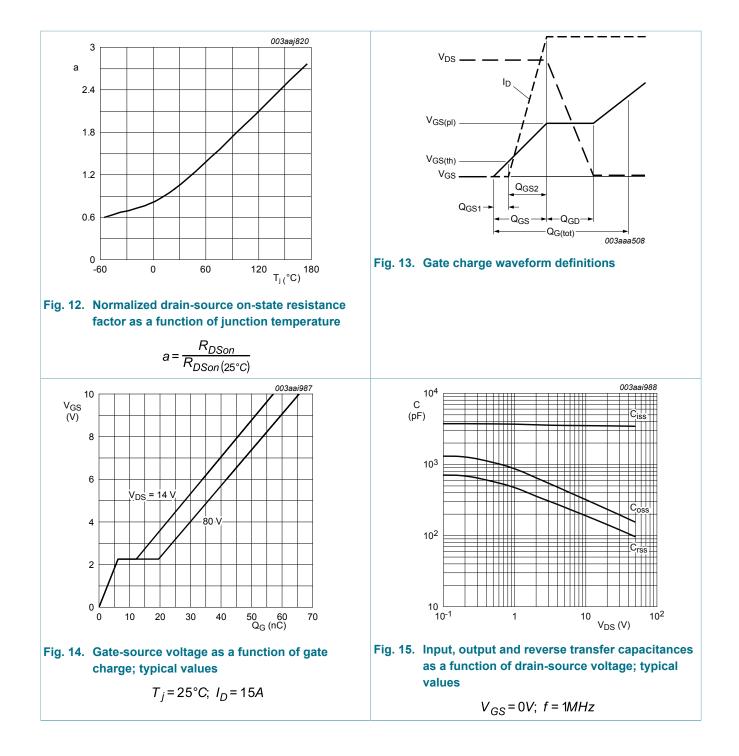
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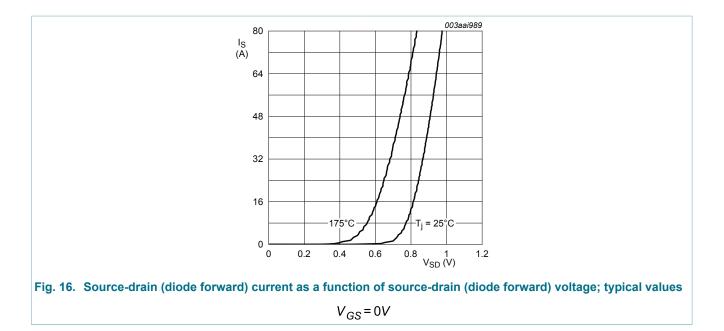
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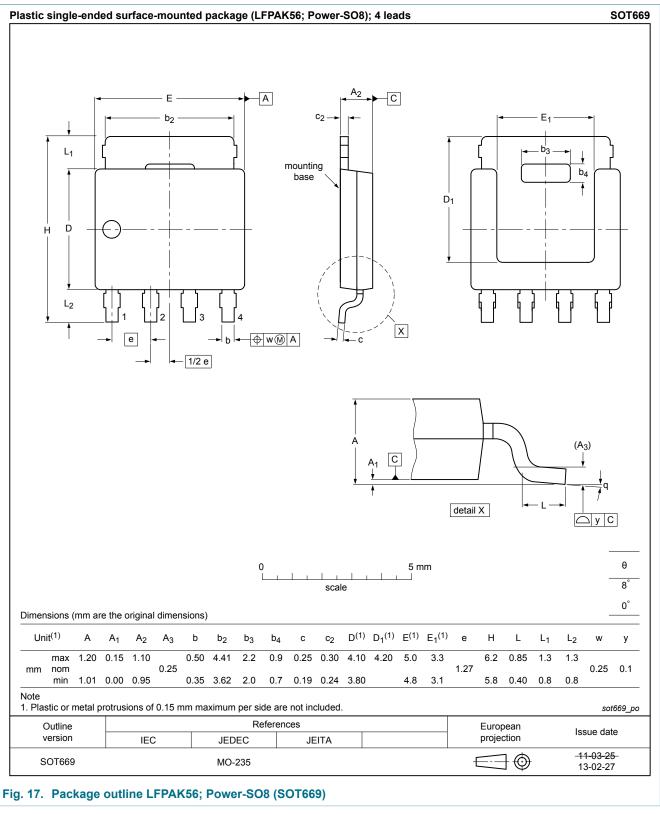
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#### N-channel 100 V, 22 mΩ logic level MOSFET in LFPAK56



#### N-channel 100 V, 22 m logic level MOSFET in LFPAK56

### 11. Package outline



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### 13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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